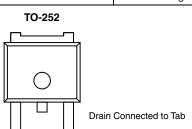


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0041			
I _D (A)	50			
Configuration	Single			

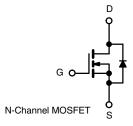


Top View

FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Material categorization:
 For definitions of compliance please see www.freescale.net.cn





ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50N04-4m1-GE3			

ABSOLUTE MAXIMUM RATING	i5 (1 _C = 25 °C, unles	s otnerwise noted	(a)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V_{DS}	40	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current ^a	T _C = 25 °C	1	50		
	T _C = 125 °C	I _D	50		
Continuous Source Current (Diode Conduction) ^a		I _S	50	Α	
Pulsed Drain Current ^b		I _{DM}	200		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	62		
Single Pulse Avalanche Energy	L = 0.1 MH	E _{AS}	192	mJ	
Martin as Barras Biratas tirah	T _C = 25 °C	D	136	W	
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	45	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		1			•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	=-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		-	3.5	\ \ \	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0030	0.0041	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0068		
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0082		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		-	120	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	5360	6700		
Output Capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	500	627	pF	
Reverse Transfer Capacitance	C _{rss}			-	250	310		
Total Gate Charge ^c	Qg			-	70	105		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_D = 50 \text{ A}$	-	16	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	13	=-		
Gate Resistance	R _g		f = 1 MHz		1.9	2.9	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	11	16		
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 0.4 \Omega$ $I_{D} \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	5	8	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	34	51		
Fall Time ^c	t _f			-	9	14		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	200	Α	
Forward Voltage	V_{SD}	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}$		_	0.9	1.5	V	

Notes

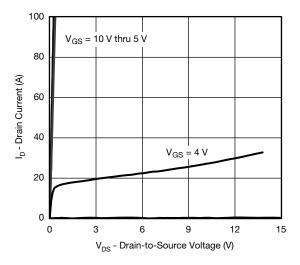
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

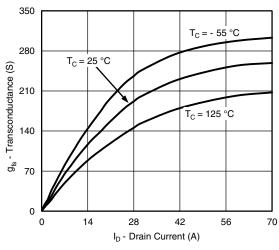


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

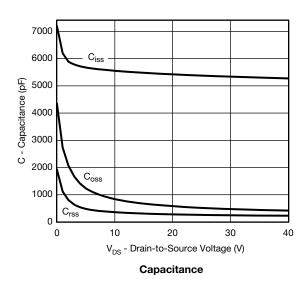
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

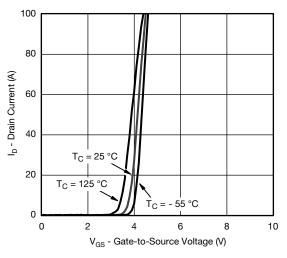


Output Characteristics

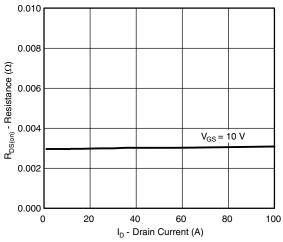


Transconductance

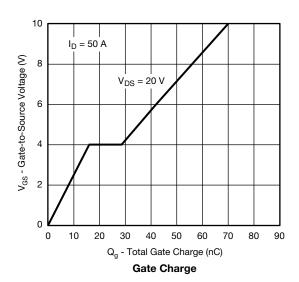




Transfer Characteristics



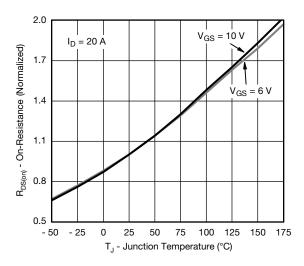
On-Resistance vs. Drain Current



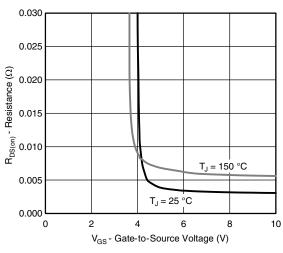


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

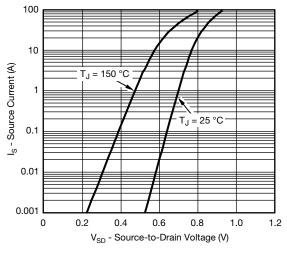
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



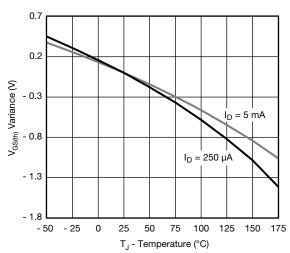
On-Resistance vs. Junction Temperature



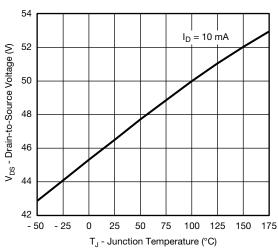
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



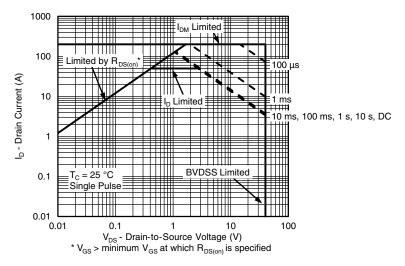
Threshold Voltage



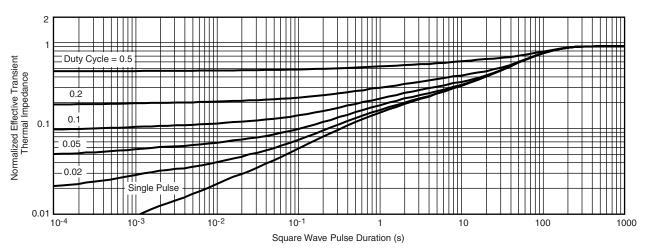
Drain Source Breakdown vs. Junction Temperature

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



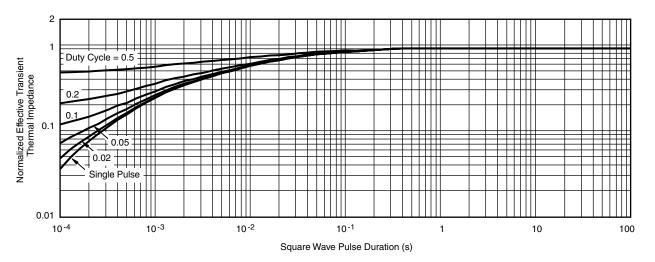
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

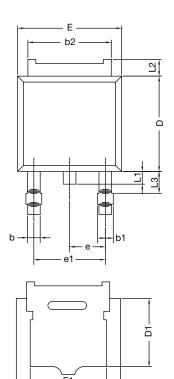
Note

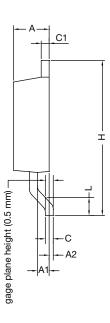
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE





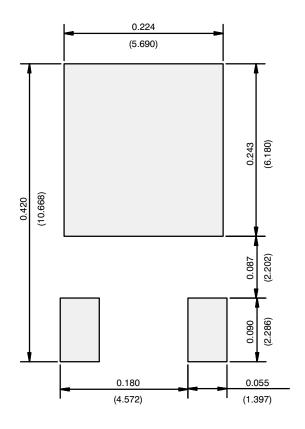
	MILLIMETERS		INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.21	2.38	0.087	0.094		
A1	0.89	1.14	0.035	0.045		
A2	0.030	0.127	0.001	0.005		
b	0.71	0.88	0.028	0.035		
b1	0.76	1.14	0.030	0.045		
b2	5.23	5.44	0.206	0.214		
С	0.46	0.58	0.018	0.023		
C1	0.46	0.58	0.018	0.023		
D	5.97	6.22	0.235	0.245		
D1	4.10	4.45	0.161	0.175		
Е	6.48	6.73	0.255	0.265		
E1	4.49	5.50	0.177	0.217		
е	2.28	BSC	0.090 BSC			
e1	4.57	BSC	0.180 BSC			
Н	9.65	10.41	0.380	0.410		
L	1.40	1.78	0.055	0.070		
L1	0.64	1.02	0.025	0.040		
L2	0.89	1.27	0.035	0.050		
L3	1.15	1.52	0.040	0.060		
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347						

Note

• Dimension L3 is for reference only.

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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Automotive N-Channel 40 V (D-S) 175 °C MOSFET

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